

SANYO	No.3813	2SJ228
		P-Channel MOS Silicon FET
Very High-Speed Switching Applications		

Features

- Small ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Meets radial taping.

Absolute Maximum Ratings at Ta = 25°C

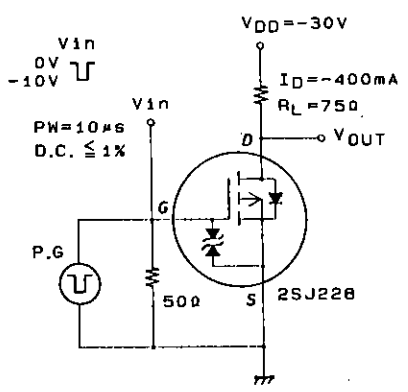
			unit
Drain to Source Voltage	V _{DSS}	-60	V
Gate to Source Voltage	V _{GSS}	±15	V
Drain Current (DC)	I _D	-0.8	A
Drain Current (Pulse)	I _{DP}	-3.2	A
Allowable Power Dissipation	P _D	1	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

PW ≤ 10μs, duty cycle ≤ 1%

Electrical Characteristics at Ta = 25°C

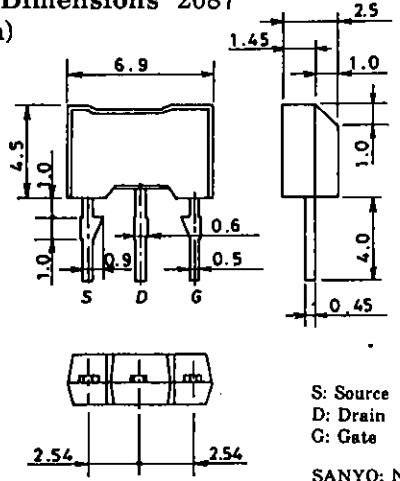
			min	typ	max	
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60V, V _{GS} = 0			-100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10V, I _D = -400mA	0.5	0.9		S
Static Drain to Source	R _{DS(on)}	I _D = -400mA, V _{GS} = -10V		0.9	1.2	Ω
on State Resistance	R _{DS(on)}	I _D = -400mA, V _{GS} = -4V		1.2	1.6	Ω
Input Capacitance	C _{iss}	V _{DS} = -20V, f = 1MHz		160		pF
Output Capacitance	C _{oss}	V _{DS} = -20V, f = 1MHz		60		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -20V, f = 1MHz		10		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		10		ns
Rise Time	t _r	"		12		ns
Turn-OFF Delay Time	t _{d(off)}	"		75		ns
Fall Time	t _f	"		30		ns
Diode Forward Voltage	V _{SD}	I _S = -800mA, V _{GS} = 0		-0.9		V

Switching Time Test Circuit

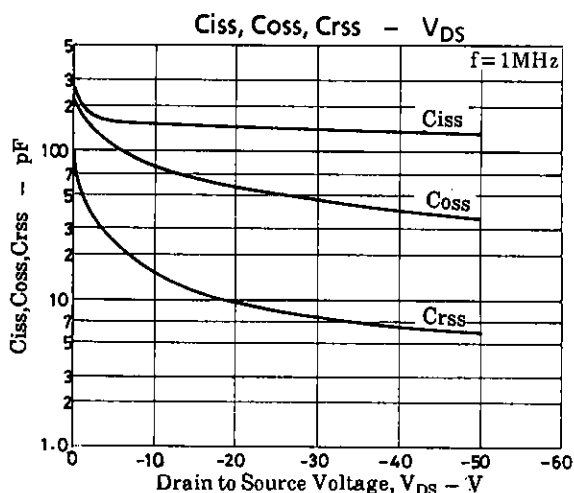
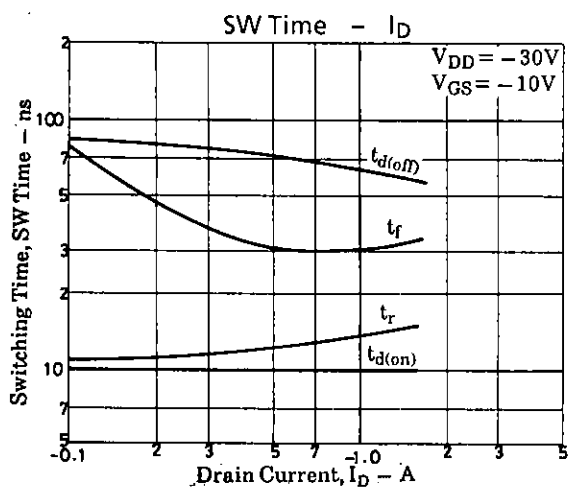
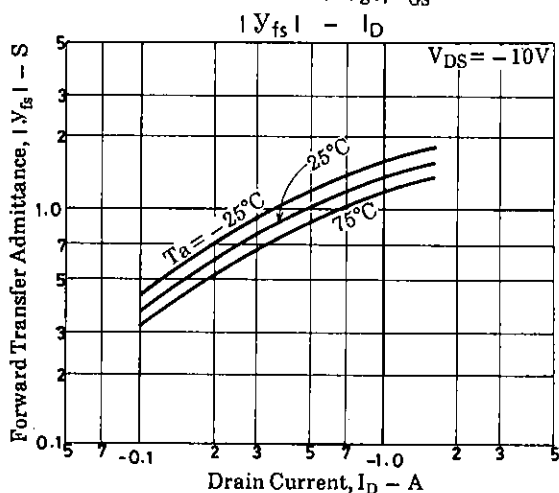
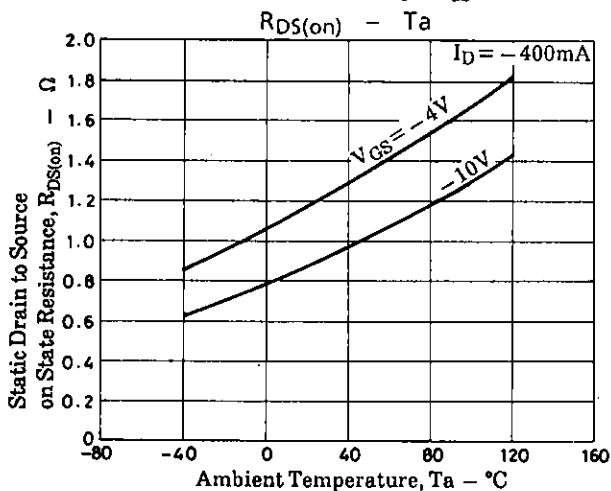
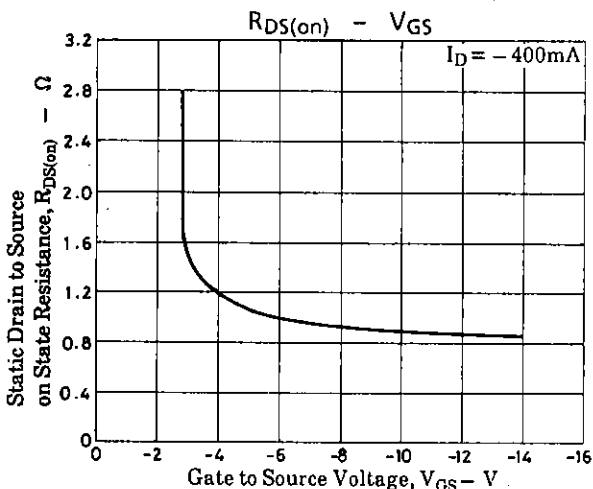
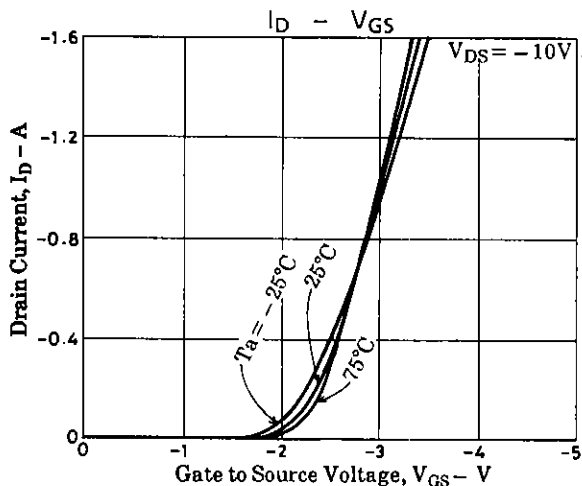
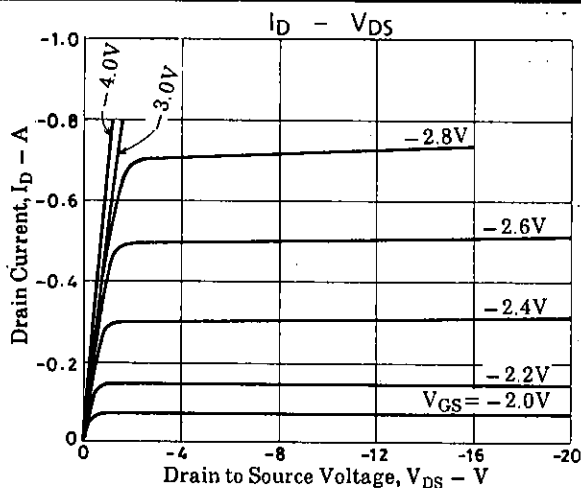
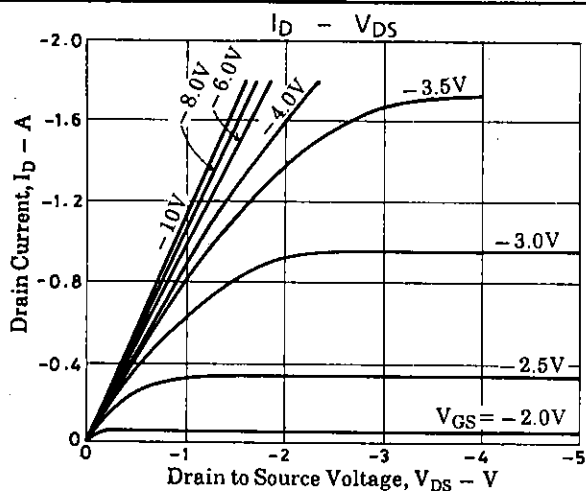


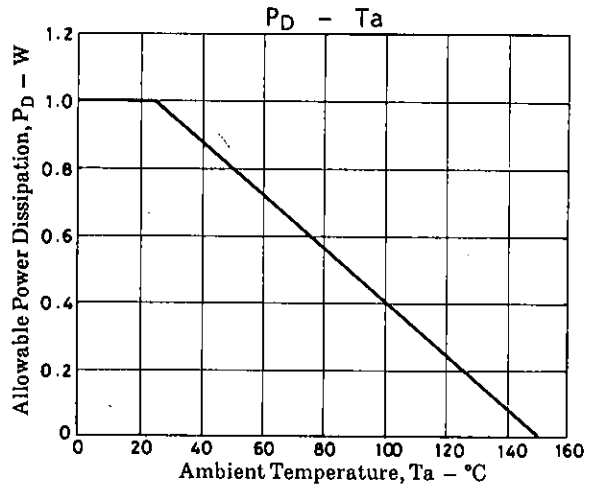
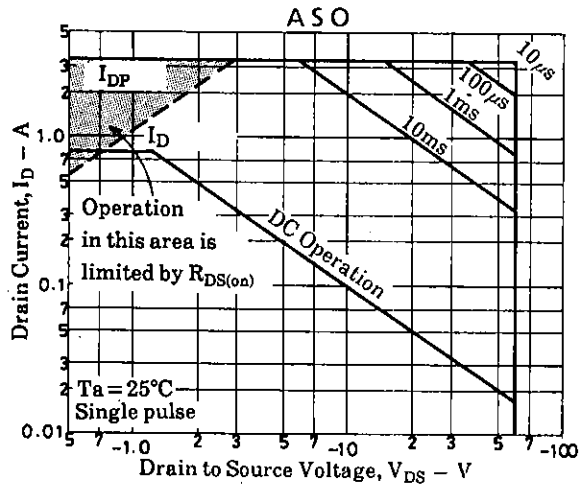
Package Dimensions 2087

(unit: mm)



S: Source
D: Drain
G: Gate
SANYO: NMP





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